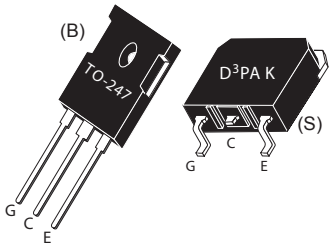
Microsemi
POWER PRODUCTS GROUP

APT25GR120B
APT25GR120S

1200V, 25A, $V_{ce(on)}$ = 2.5V Typical

Ultra Fast NPT - IGBT®



The Ultra Fast NPT - IGBT® family of products is the newest generation of planar IGBTs optimized for outstanding ruggedness and the best trade-off between conduction and switching losses.

Features

- **Low Saturation Voltage**
- **Low Tail Current**
- **RoHS Compliant**
- **Short Circuit Withstand Rated**
- **High Frequency Switching**
- **Ultra Low Leakage Current**

Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{ces}	Collector Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current @ T_C = 25°C	75	A
I_{C2}	Continuous Collector Current @ T_C = 125°C	25	
I_{CM}	Pulsed Collector Current ①	100	
SCWT	Short Circuit Withstand Time: V_{CE} = 600V, V_{GE} = 15V, T_C=125°C	10	µs
P_D	Total Power Dissipation @ T_C = 25°C	521	W
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 500µA)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 1.0mA, T_j = 25°C)	3.5	5.0	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 25A, T_j = 25°C)		2.5	3.2	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 25A, T_j = 125°C)		3.3		
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 50A, T_j = 25°C)		3.5		
I_{CES}	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 25°C) ②		5	500	µA
	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 125°C) ②		50		
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			±250	nA

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT25GR120B_S

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance		2784		pF
C_{oes}	Output Capacitance	V_{GE} = 0V, V_{CE} = 25V		271		
C_{res}	Reverse Transfer Capacitance	f = 1MHz		75		
V_{GEP}	Gate to Emitter Plateau Voltage	Gate Charge		7.5		V
Q_g ③	Total Gate Charge	V_{GE} = 15V		154	203	nC
Q_{ge}	Gate-Emitter Charge	V_{CE}= 600V		20	27	
Q_{gc}	Gate- Collector Charge	I_C = 25A		76	97	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C)		16		ns
t_r	Current Rise Time	V_{CC} = 600V		10		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		122		
t_f	Current Fall Time	I_C = 25A		20		
E_{on2} ⑤	Turn-On Switching Energy	R_G = 4.3 Ω④		742	1110	µJ
E_{off} ⑥	Turn-Off Switching Energy	T_J = +25°C		427	640	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C)		16		ns
t_r	Current Rise Time	V_{CC} = 600V		10		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		136		
t_f	Current Fall Time	I_C = 25A		28		
E_{on2} ⑤	Turn-On Switching Energy	R_G = 4.3 Ω④		1297	1945	µJ
E_{off} ⑥	Turn-Off Switching Energy	T_J = +125°C		480	720	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			.24	°C/W
$R_{\theta JA}$	Junction to Ambient Thermal Resistance			40	
W_T	Package Weight		.22		oz
			6.2		g
Torque	Mounting Torque (TO-247 Package), 4-40 or M3 screw			10	in-lbf
				6.2	N·m

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width < 380μs, duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

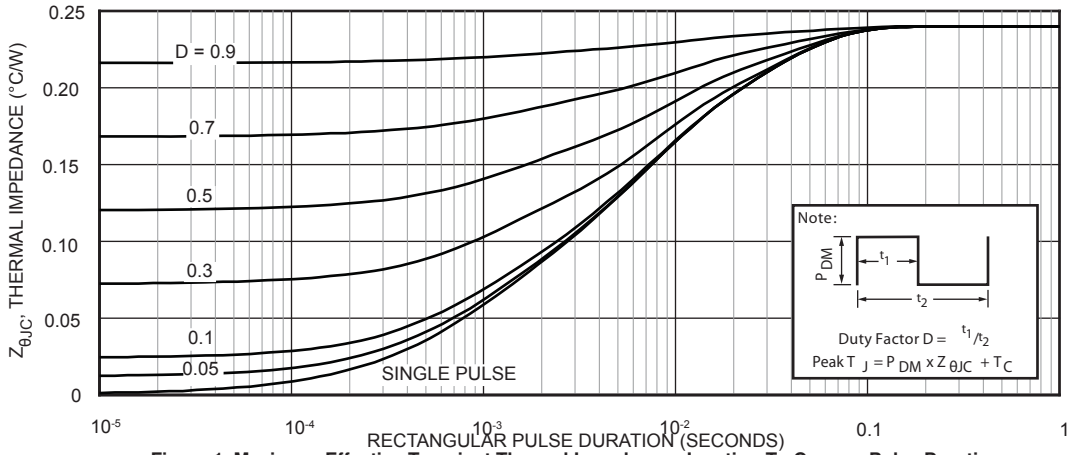


Figure 1, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

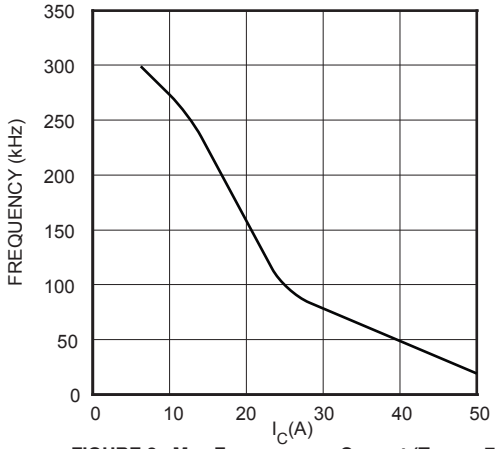


FIGURE 2, Max Frequency vs Current (T_{case} = 75°C)

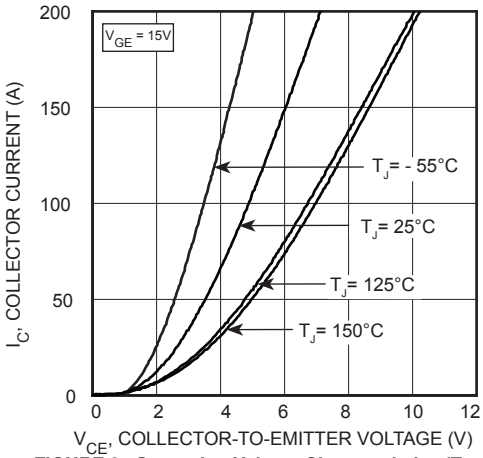


FIGURE 3, Saturation Voltage Characteristics (T_J = 25°C)

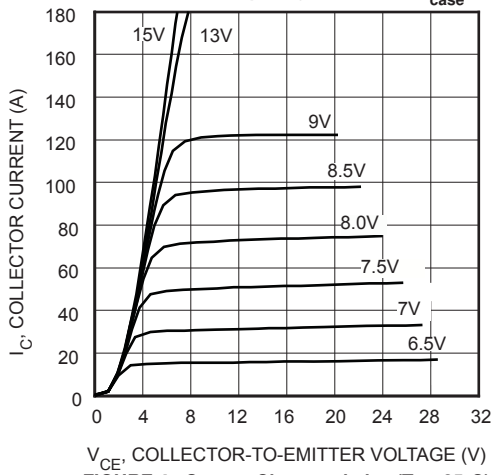


FIGURE 4, Output Characteristics (T_J = 25°C)

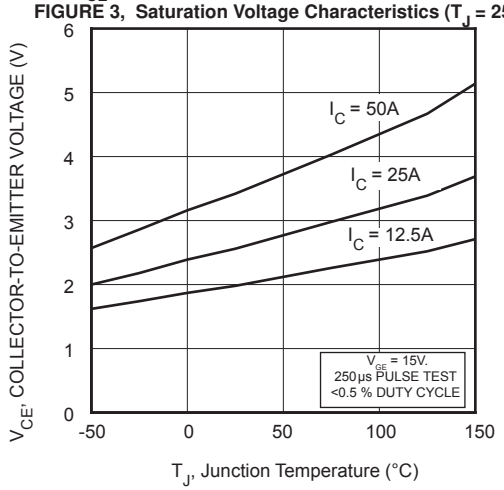


FIGURE 5, On State Voltage vs Junction Temperature

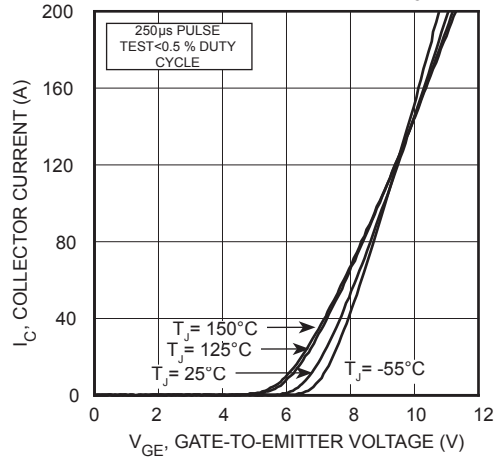


FIGURE 6, Transfer Characteristics

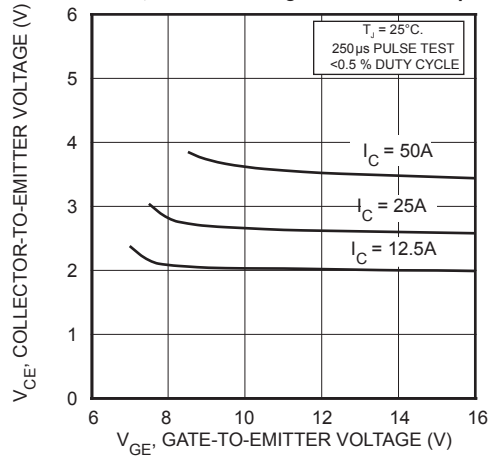


FIGURE 7, On State Voltage vs Gate-to-Emitter Voltage

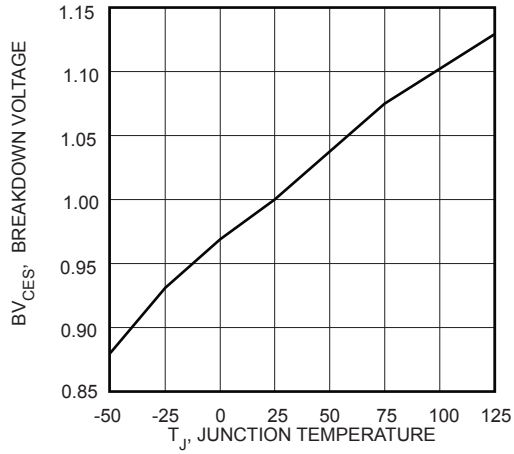


FIGURE 8, Breakdown Voltage vs Junction Temperature

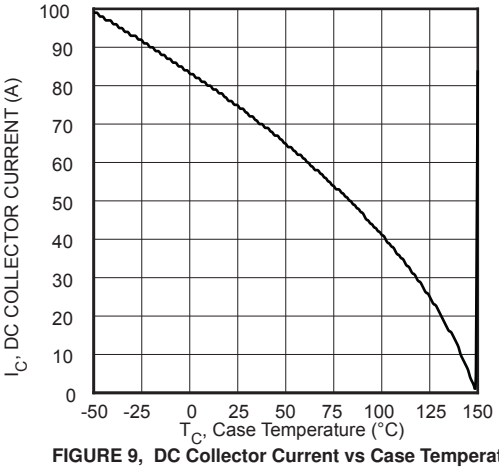


FIGURE 9, DC Collector Current vs Case Temperature

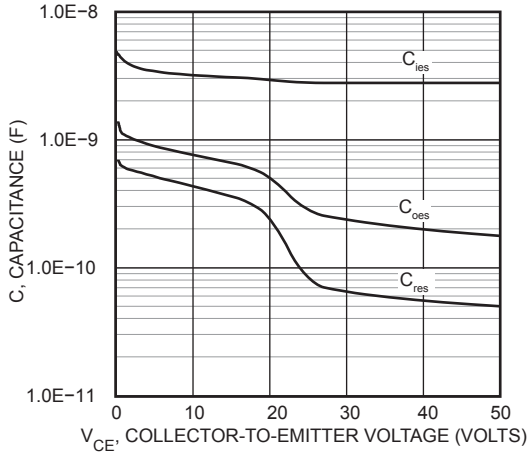


FIGURE 10, Capacitance vs Collector-To-Emitter Voltage

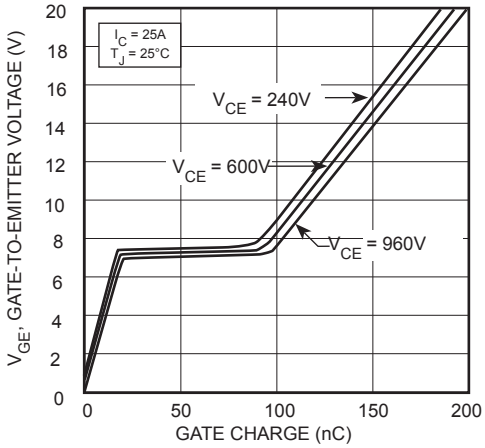


FIGURE 11, Gate charge

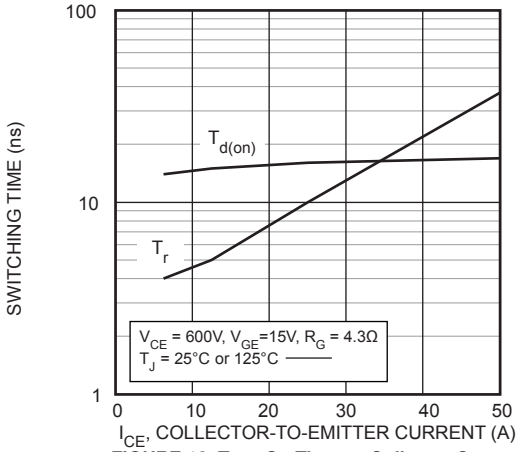


FIGURE 12, Turn-On Time vs Collector Current

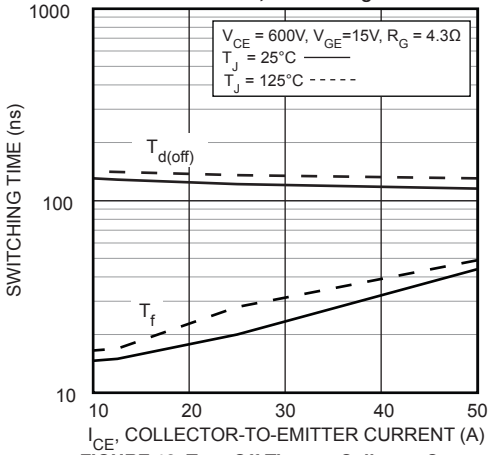


FIGURE 13, Turn-Off Time vs Collector Current

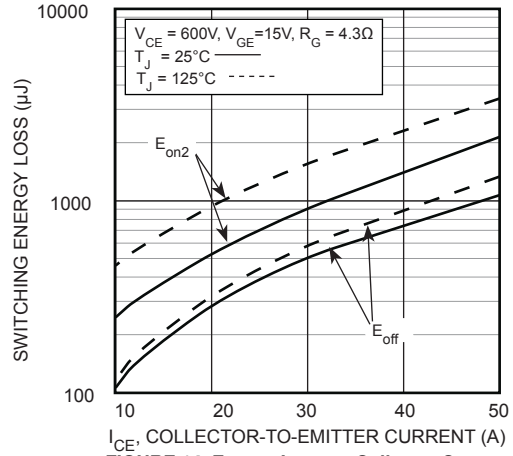


FIGURE 14, Energy Loss vs Collector Current

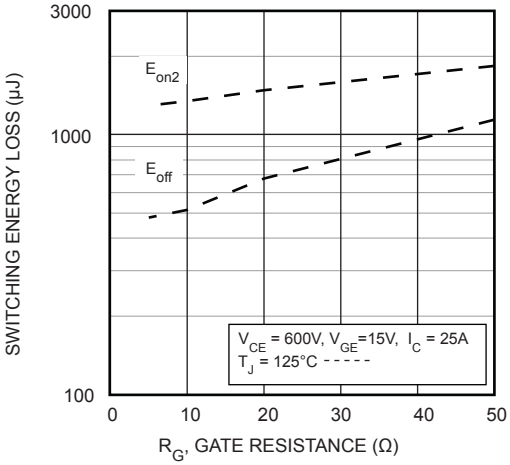


FIGURE 15, Energy Loss vs Gate Resistance

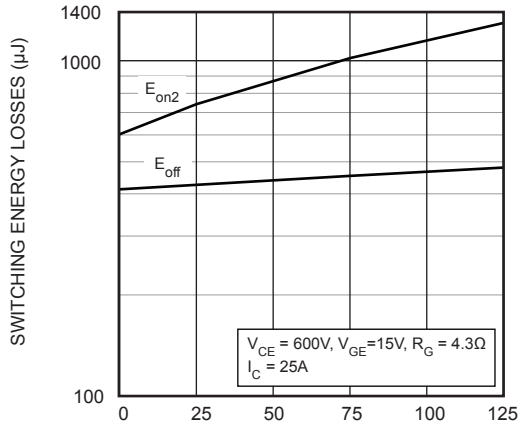


FIGURE 16, Switching Energy vs Junction Temperature

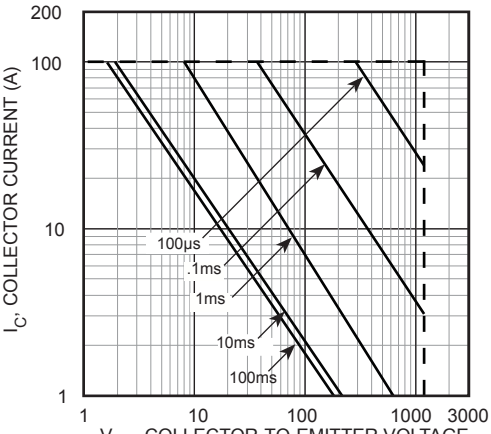
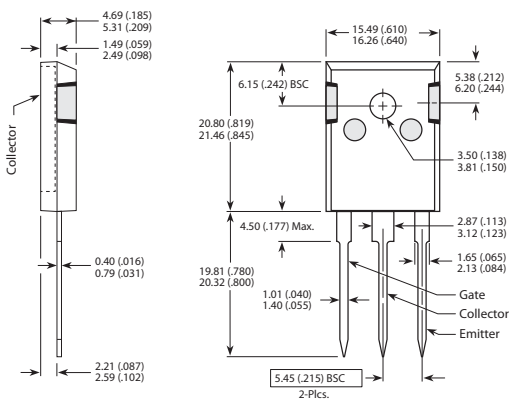


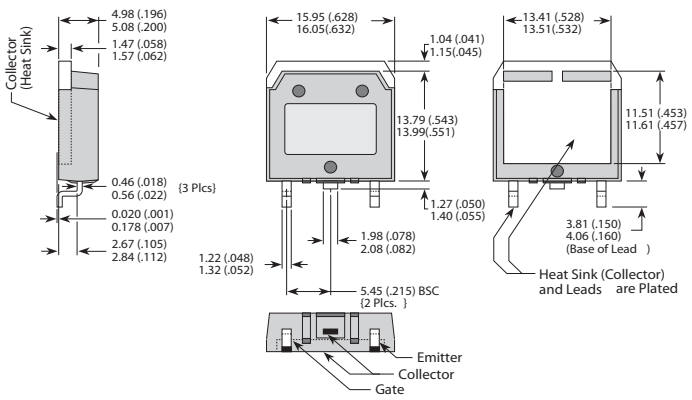
FIGURE 17, Minimum Switching Safe Operating Area

TO-247 Package Outline



Dimensions in Millimeters (Inches)

D³PAK Package Outline



Dimensions in Millimeters (Inches)

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